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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

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Serial No.: 10/828,958

Filed: April 20, 2004

For: A METHOD FOR MAKING A
SEMICONDUCTOR DEVICE
HAVING A HIGH-K GATE
DIELECTRIC LAYER AND A
METAL GATE ELECTRODE

Art Unit: 2812

Examiner: unknown

Attorney Docket: P18609

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT

Sir:

This Information Disclosure Statement is being submitted under 37 C.F.R. §1.97(b). Enclosed is a copy of Information Disclosure Citation Form PTO-1449 together with a copy of the reference cited on that form. It is respectfully requested that the cited reference be considered and that the enclosed copy of Information Disclosure Citation Form PTO-1449 be initialed by the Examiner to indicate such consideration and a copy thereof returned to applicant(s).

Pursuant to 37 C.F.R. § 1.97, the submission of this Information Disclosure Statement is not to be construed as a representation that a search has been made

and is not to be construed as an admission that the information cited in this statement constitutes prior art or is otherwise material to patentability.

Respectfully submitted,

Dated: Oct. 5, 2004

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(37 C.F.R. § 1.8(a))

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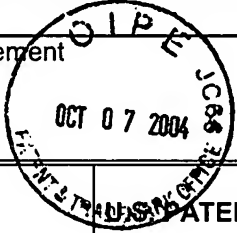
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Signature

Oct. 5, 2004
Date

Form PTO-1449 (Modified)		Atty Docket No.: P18609		Serial No.: 10/828,958	
List of Patents and Publications Statement (Use several sheets if necessary)				Applicant: Justin K. Brask et al.	
				Filing Date: April 20, 2004	



REFERENCE DESIGNATION						
Examiner Initials		Document No.		Class	Sub-Class	Filing date if appropriate
	AA	6,255,698 B1	Gardner et al.	257	369	
	AB	6,410,376 B1	Ng et al.	438	199	
	AC	6,586,288 B2	Kim et al.	438	183	
	AD	US 2002/0058374 A1	Kim et al.	438	228	
	AE					
	AF					
	AG					
	AH					
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	AJ					
	AK					
	AL					
	AM					
	AN					
	AO					

FOREIGN PATENT DOCUMENTS							
		Document No.	Date	Country	Class	Sub-Class	Translation
	AP	EP 0 899 784 AZ	3/3/1999				
	AQ	GB 2 358 737 A	4/24/2001				
	AR						

OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.)		
	AS	Metz et al., "A Method for Making a Semiconductor Device Having a High-K Gate Dielectric Layer and a Metal Gate Electrode", Serial No. 10/839,077, Filed May 4, 2004
	AT	
	AU	
	AV	
	AW	
	AX	
	AY	
	AZ	

Examiner	Date Considered
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EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.